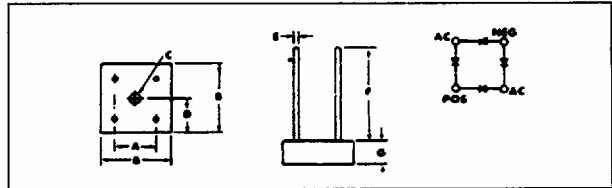


HERB High Efficiency Rectifier Bridges 7 Amp.

Designed for High Frequency Switching Power Supply Applications
Extremely Low Leakage at High Temperatures
High Surge Capability
Low Cost Epoxy Encapsulation
Glass Passivation

LTR.	INCHES	MILLIMETERS
A	.411-.441	10,44-11,20
B	.590-.610	14,99-15,49
C	.137-.167 Dia.	3,48-4,24 Dia.
D	.295-.305	7,49-7,75
E	.037-.043 Dia.	.94-1,09 Dia.
F	1.0 Min.	25,4 Min.
G	.195-.205	4,95-5,21



MAXIMUM RATINGS (At 25°C unless otherwise noted)

RATINGS	SYMBOL	VH048H	VH148H	VH248H
DC Blocking Voltage	V_{RM}	50V	100V	200V
Working Peak Reverse Voltage	V_{RWM}			
Peak Repetitive Reverse Voltage	V_{RRM}			
RMS Reverse Voltage	$V_{R(RMS)}$	35V	70V	140V
Peak Surge Current, 1/2 Cycle at 60 Hz, (non-rep) $T_{HS} = 80^{\circ}C$	I_{FSM}	150 Amps		
Average Rectified Output Current	I_O	7 Amp @ $T_{HS} = 80^{\circ}C$		
Junction Operating and Storage Temperature		- 50 to + 150°C		
Maximum Soldering Temperature & Time		10 Sec. at 265°C		

ELECTRICAL CHARACTERISTICS (At $T_A = 25^{\circ}C$ unless otherwise noted)

Maximum Instantaneous Forward Voltage Drop per Diode at 7 Amp.	V_{FM}	0.95 V @ $T_J = 25^{\circ}C$ 0.875 V @ $T_J = 100^{\circ}C$
Maximum Reverse Recovery Time $I_F = .5A, I_R = 1A, I_{RR} = .25A$	t_{rr}	30nS
Maximum Reverse Current at Rated V_{RM}	I_{RM}	5.0 μ A @ $T_J = 25^{\circ}C$ 150 μ A @ $T_J = 150^{\circ}C$
Typical Junction Capacitance (1MHz, $V_R = -10V$) per individual diode	C_T	75 pF
Insulation Strength From Circuit to Case (min.)		2000VDC

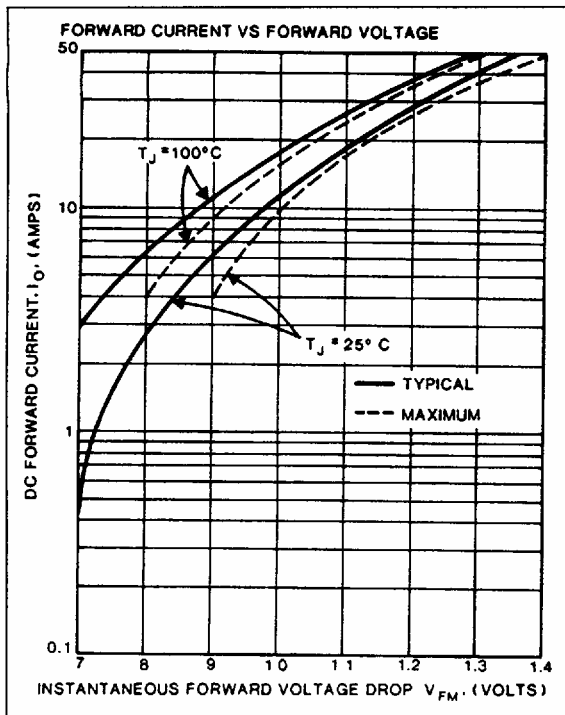


FIGURE 1

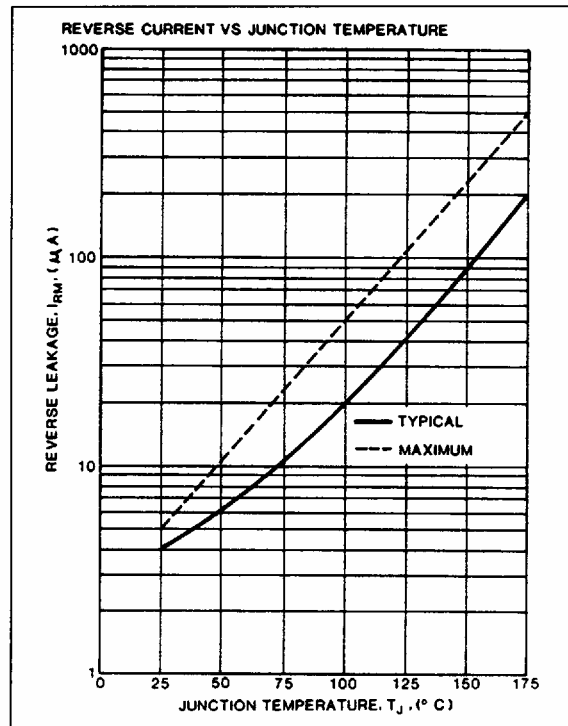


FIGURE 2

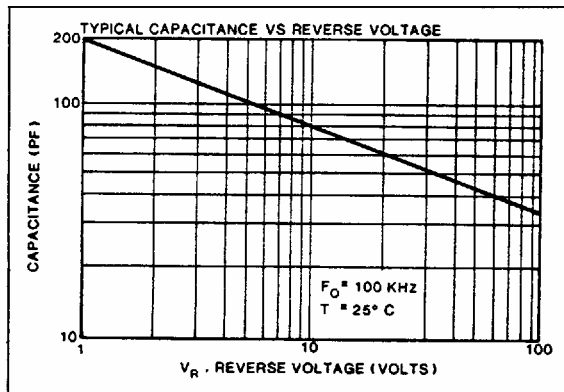


FIGURE 3

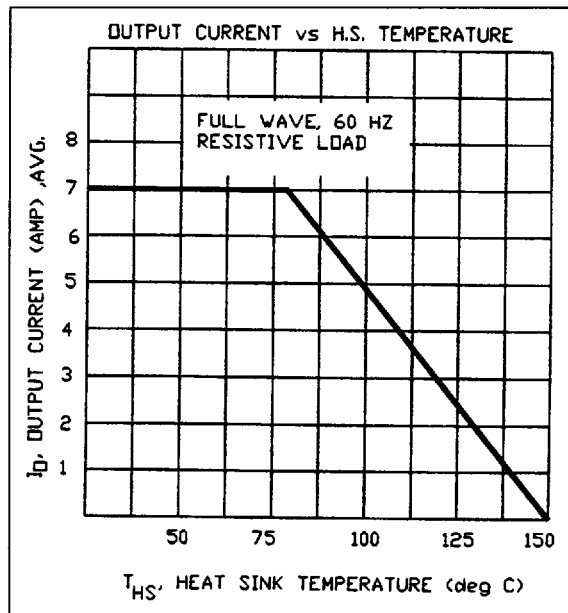


FIGURE 4